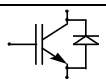


Elektrische Eigenschaften / Electrical properties

Höchstzulässige Werte / Maximum rated values

Diode Gleichrichter/ Diode Rectifier

Periodische Rückw. Spitzensperrspannung repetitive peak reverse voltage		V_{RRM}	1600	V
Durchlaßstrom Grenzeffektivwert RMS forward current per chip		I_{FRMSM}	40	A
Dauergleichstrom DC forward current	T_C = 80°C	I_d	30	A
Stoßstrom Grenzwert surge forward current	t_P = 10 ms, T_{vj} = 25°C t_P = 10 ms, T_{vj} = 150°C	I_{FSM}	300 230	A A
Grenzlastintegral I^2t - value	t_P = 10 ms, T_{vj} = 25°C t_P = 10 ms, T_{vj} = 150°C	I^2t	450 260	A^2s A^2s

Transistor Wechselrichter/ Transistor Inverter

Kollektor-Emitter-Sperrspannung collector-emitter voltage		V_{CES}	600	V
Kollektor-Dauergleichstrom DC-collector current	Tc = 80 °C T_C = 25 °C	$I_{C,nom.}$ I_C	30 50	A A
Periodischer Kollektor Spitzenstrom repetitive peak collector current	t_P = 1 ms, T_C = 80 °C	I_{CRM}	60	A
Gesamt-Verlustleistung total power dissipation	T_C = 25°C	P_{tot}	180	W
Gate-Emitter-Spitzenspannung gate-emitter peak voltage		V_{GES}	+/- 20V	V

Diode Wechselrichter/ Diode Inverter

Dauergleichstrom DC forward current	Tc = 80 °C	I_F	30	A
Periodischer Spitzenstrom repetitive peak forw. current	t_P = 1 ms	I_{FRM}	60	A
Grenzlastintegral I^2t - value	V_R = 0V, t_p = 10ms, T_{vj} = 125°C	I^2t	240	A^2s

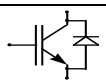
Transistor Brems-Chopper/ Transistor Brake-Chopper

Kollektor-Emitter-Sperrspannung collector-emitter voltage		V_{CES}	600	V
Kollektor-Dauergleichstrom DC-collector current	T_C = 80 °C T_C = 25 °C	$I_{C,nom.}$ I_C	15 25	A A
Periodischer Kollektor Spitzenstrom repetitive peak collector current	t_P = 1 ms, T_C = 80°C	I_{CRM}	30	A
Gesamt-Verlustleistung total power dissipation	T_C = 25°C	P_{tot}	100	W
Gate-Emitter-Spitzenspannung gate-emitter peak voltage		V_{GES}	+/- 20V	V

Diode Brems-Chopper/ Diode Brake-Chopper

Dauergleichstrom DC forward current	Tc = 80 °C	I_F	10	A
Periodischer Spitzenstrom repetitive peak forw. current	t_P = 1 ms	I_{FRM}	20	A

prepared by: Andreas Schulz	date of publication:17.09.1999
approved by: M.Hierholzer	revision: 4



Modul Isolation/ Module Isolation

Isolations-Prüfspannung insulation test voltage	RMS, f = 50 Hz, t = 1 min. NTC connected to Baseplate	V_{ISOL}		2,5	kV

Elektrische Eigenschaften / Electrical properties

Charakteristische Werte / Characteristic values

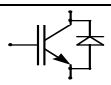
Diode Gleichrichter/ Diode Rectifier			**min.**	**typ.**	**max.**	
Durchlaßspannung forward voltage	T_{vj} = 150°C, I_F = 30 A	V_F	-	1,1	1,15	V
Schleusenspannung threshold voltage	T_{vj} = 150°C	$V_{(TO)}$	-	-	0,8	V
Ersatzwiderstand slope resistance	T_{vj} = 150°C	r_T	-	-	10,5	mΩ
Sperrstrom reverse current	T_{vj} = 150°C, V_R = 1600 V	I_R	-	2	-	mA
Modul Leitungswiderstand, Anschlüsse-Chip lead resistance, terminals-chip	T_C = 25°C	$R_{AA'+CC'}$	-	8	-	mΩ

Transistor Wechselrichter/ Transistor Inverter			**min.**	**typ.**	**max.**	
Kollektor-Emitter Sättigungsspannung collector-emitter saturation voltage	V_{GE} = 15V, T_{vj} = 25°C, I_C = 30 A V_{GE} = 15V, T_{vj} = 125°C, I_C = 30 A	$V_{CE\ sat}$	- -	1,95 2,2	2,45 -	V V
Gate-Schwellenspannung gate threshold voltage	$V_{CE} = V_{GE}$, T_{vj} = 25°C, I_C = 0,7 mA	$V_{GE(TO)}$	4,5	5,5	6,5	V
Eingangskapazität input capacitance	f = 1MHz, T_{vj} = 25°C V_{CE} = 25 V, V_{GE} = 0 V	C_{ies}	-	1,6	-	nF
Kollektor-Emitter Reststrom collector-emitter cut-off current	V_{GE} = 0V, T_{vj} = 25°C, V_{CE} = 600 V V_{GE} = 0V, T_{vj} =125°C, V_{CE} = 600 V	I_{CES}	- -	1,0 1,2	500 -	µA mA
Gate-Emitter Reststrom gate-emitter leakage current	V_{CE} = 0V, V_{GE} =20V, T_{vj} =25°C	I_{GES}	-	-	300	nA
Einschaltverzögerungszeit (ind. Last) turn on delay time (inductive load)	$I_C = I_{Nenn}$, V_{CC} = 300 V V_{GE} = ±15V, T_{vj} = 25°C, R_G = 33 Ohm V_{GE} = ±15V, T_{vj} = 125°C, R_G = 33 Ohm	$t_{d,on}$	- -	50 50	- -	ns ns
Anstiegszeit (induktive Last) rise time (inductive load)	$I_C = I_{Nenn}$, V_{CC} = 300 V V_{GE} = ±15V, T_{vj} = 25°C, R_G = 33 Ohm V_{GE} = ±15V, T_{vj} = 125°C, R_G = 33 Ohm	t_r	- -	50 50	- -	ns ns
Abschaltverzögerungszeit (ind. Last) turn off delay time (inductive load)	$I_C = I_{Nenn}$, V_{CC} = 300 V V_{GE} = ±15V, T_{vj} = 25°C, R_G = 33 Ohm V_{GE} = ±15V, T_{vj} = 125°C, R_G = 33 Ohm	$t_{d,off}$	- -	250 270	- -	ns ns
Fallzeit (induktive Last) fall time (inductive load)	$I_C = I_{Nenn}$, V_{CC} = 300 V V_{GE} = ±15V, T_{vj} = 25°C, R_G = 33 Ohm V_{GE} = ±15V, T_{vj} = 125°C, R_G = 33 Ohm	t_f	- -	30 40	- -	ns ns
Einschaltverlustenergie pro Puls turn-on energy loss per pulse	$I_C = I_{Nenn}$, V_{CC} = 300 V V_{GE} = ±15V, T_{vj} = 125°C, R_G = 33 Ohm L_S = 75 nH	E_{on}	-	1,4	-	mWs
Abschaltverlustenergie pro Puls turn-off energy loss per pulse	$I_C = I_{Nenn}$, V_{CC} = 300 V V_{GE} = ±15V, T_{vj} = 125°C, R_G = 33 Ohm L_S = 75 nH	E_{off}	-	1	-	mWs
Kurzschlußverhalten SC Data	$t_P \leq 10\mu s$, $V_{GE} \leq 15V$, R_G = 33 Ohm $T_{vj} \leq 125°C$, V_{CC} = 360 V dI/dt = 1800 A/µs	I_{SC}	-	120	-	A

Elektrische Eigenschaften / Electrical properties

Charakteristische Werte / Characteristic values

			min.	typ.	max.	
Modulinduktivität stray inductance module		$L_{\sigma CE}$	-	-	100	nH
Modul Leitungswiderstand, Anschlüsse-Chip lead resistance, terminals-chip	T_C = 25°C	$R_{CC'+EE'}$	-	11	-	mΩ
Diode Wechselrichter/ Diode Inverter			**min.**	**typ.**	**max.**	
Durchlaßspannung forward voltage	V_{GE} = 0V, T_{vj} = 25°C, I_F = 30 A	V_F	-	1,25	1,7	V
	V_{GE} = 0V, T_{vj} = 125°C, I_F = 30 A		-	1,2	-	V
Rückstromspitze peak reverse recovery current	I_F=I_{Nenn}, - di_F/dt = 900A/µs					
	V_{GE} = -10V, T_{vj} = 25°C, V_R = 300 V	I_{RM}	-	26	-	A
	V_{GE} = -10V, T_{vj} = 125°C, V_R = 300 V		-	34	-	A
Sperrverzögerungsladung recovered charge	I_F=I_{Nenn}, - di_F/dt = 900A/µs					
	V_{GE} = -10V, T_{vj} = 25°C, V_R = 300 V	Q_r	-	2,5	-	µAs
	V_{GE} = -10V, T_{vj} = 125°C, V_R = 300 V		-	4	-	µAs
Abschaltenergie pro Puls reverse recovery energy	I_F=I_{Nenn}, - di_F/dt = 900A/µs					
	V_{GE} = -10V, T_{vj} = 25°C, V_R = 300 V	E_{RQ}	-	0,5	-	mWs
	V_{GE} = -10V, T_{vj} = 125°C, V_R = 300 V		-	0,8	-	mWs
Transistor Brems-Chopper/ Transistor Brake-Chopper			**min.**	**typ.**	**max.**	
Kollektor-Emitter Sättigungsspannung collector-emitter saturation voltage	V_{GE} = 15V, T_{vj} = 25°C, I_C = 15,0 A	$V_{CE\ sat}$	-	1,95	2,45	V
	V_{GE} = 15V, T_{vj} = 125°C, I_C = 15,0 A		-	2,2	-	V
Gate-Schwellenspannung gate threshold voltage	V_{CE} = V_{GE}, T_{vj} = 25°C, I_C = 0,4 mA	$V_{GE(TO)}$	4,5	5,5	6,5	V
Eingangskapazität input capacitance	f = 1MHz, T_{vj} = 25°C V_{CE} = 25 V, V_{GE} = 0 V	C_{ies}	-	0,8	-	nF
Kollektor-Emitter Reststrom collector-emitter cut-off current	V_{GE} = 0V, T_{vj} = 25°C, V_{CE} = 600 V	I_{CES}	-	0,5	500	µA
	V_{GE} = 0V, T_{vj} = 125°C, V_{CE} = 600 V		-	0,8	-	mA
Gate-Emitter Reststrom gate-emitter leakage current	V_{CE} = 0V, V_{GE} = 20V, T_{vj} = 25°C	I_{GES}	-	-	300	nA
Diode Brems-Chopper/ Diode Brake-Chopper			**min.**	**typ.**	**max.**	
Durchlaßspannung forward voltage	T_{vj} = 25°C, I_F = 15,0 A	V_F	-	1,4	1,95	V
	T_{vj} = 125°C, I_F = 15,0 A		-	1,35	-	V
NTC-Widerstand/ NTC-Thermistor			**min.**	**typ.**	**max.**	
Nennwiderstand rated resistance	T_C = 25°C	R_{25}	-	5	-	kΩ
Abweichung von R_{100} deviation of R_{100}	T_C = 100°C, R_{100} = 493 Ω	ΔR/R	-5		5	%
Verlustleistung power dissipation	T_C = 25°C	P_{25}			20	mW
B-Wert B-value	$R_2 = R_1 \exp [B(1/T_2 - 1/T_1)]$	$B_{25/50}$		3375		K



Thermische Eigenschaften / Thermal properties

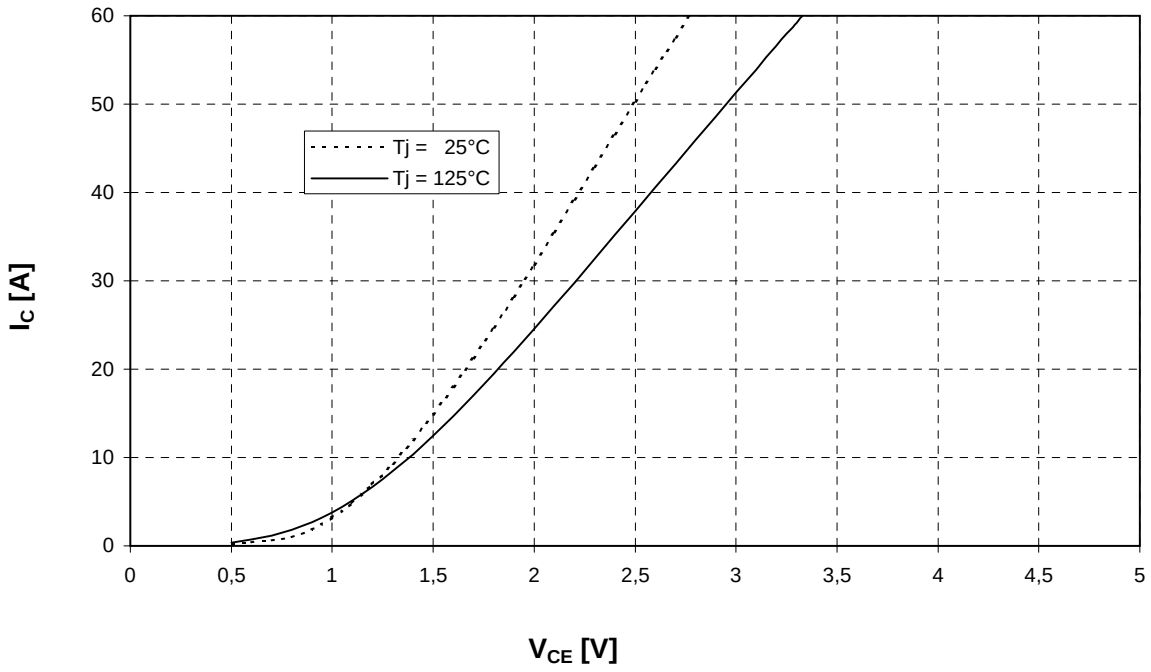
				min.	typ.	max.	
Innerer Wärmewiderstand thermal resistance, junction to case	Gleichr. Diode/ Rectif. Diode		R_{thJC}	-	-	1	K/W
	Trans. Wechsr./ Trans. Inverter			-	-	0,7	K/W
	Diode Wechsr./ Diode Inverter			-	-	1,2	K/W
	Trans. Bremse/ Trans. Brake			-	-	1,3	K/W
	Diode Bremse/ Diode Brake			-	-	2,3	K/W
Übergangs-Wärmewiderstand thermal resistance, case to heatsink	Gleichr. Diode/ Rectif. Diode	λ_{Paste}=1W/m*K	R_{thCK}	-	0,08	-	K/W
	Trans. Wechsr./ Trans. Inverter	λ_{grease}=1W/m*K		-	0,04	-	K/W
	Diode Wechsr./ Diode Inverter			-	0,08	-	K/W
Höchstzulässige Sperrschichttemperatur maximum junction temperature			T_{vj}	-	-	150	°C
Betriebstemperatur operation temperature			T_{op}	-40	-	125	°C
Lagertemperatur storage temperature			T_{stg}	-40	-	125	°C

Mechanische Eigenschaften / Mechanical properties

Innere Isolation internal insulation			Al_2O_3		
CTI comperative tracking index			225		
Anzugsdrehmoment f. mech. Befestigung mounting torque		M	3 ±10%		Nm
Gewicht weight		G	180		g

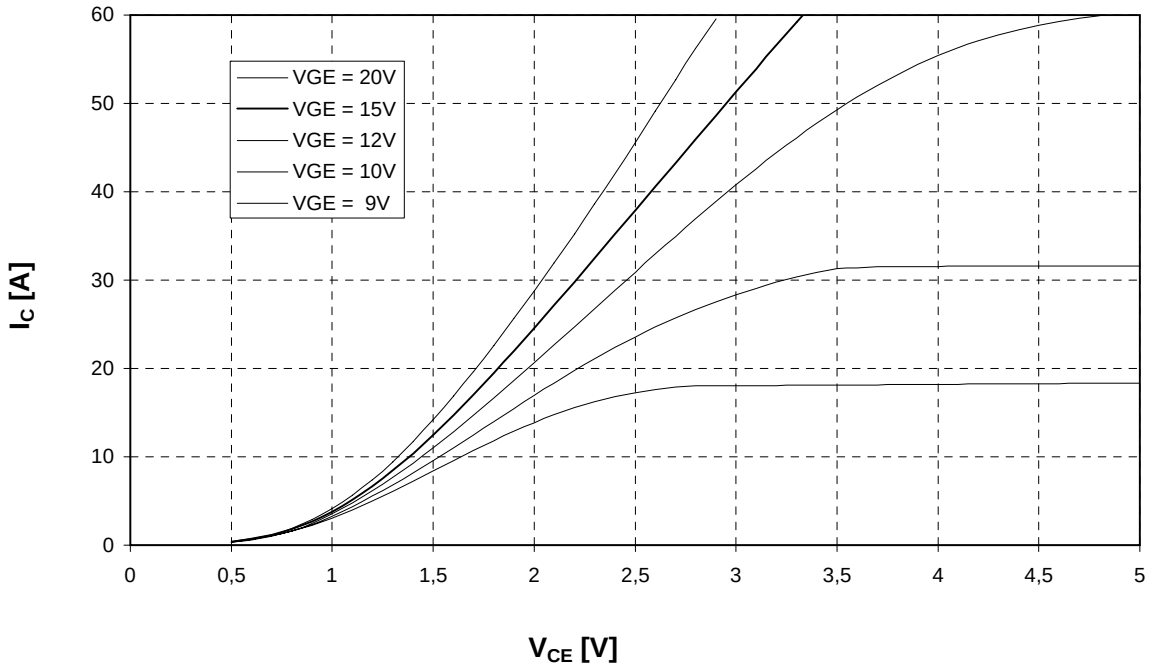
Ausgangskennlinienfeld Wechselr. (typisch) $I_C = f(V_{CE})$

Output characteristic Inverter (typical) $V_{GE} = 15\ V$



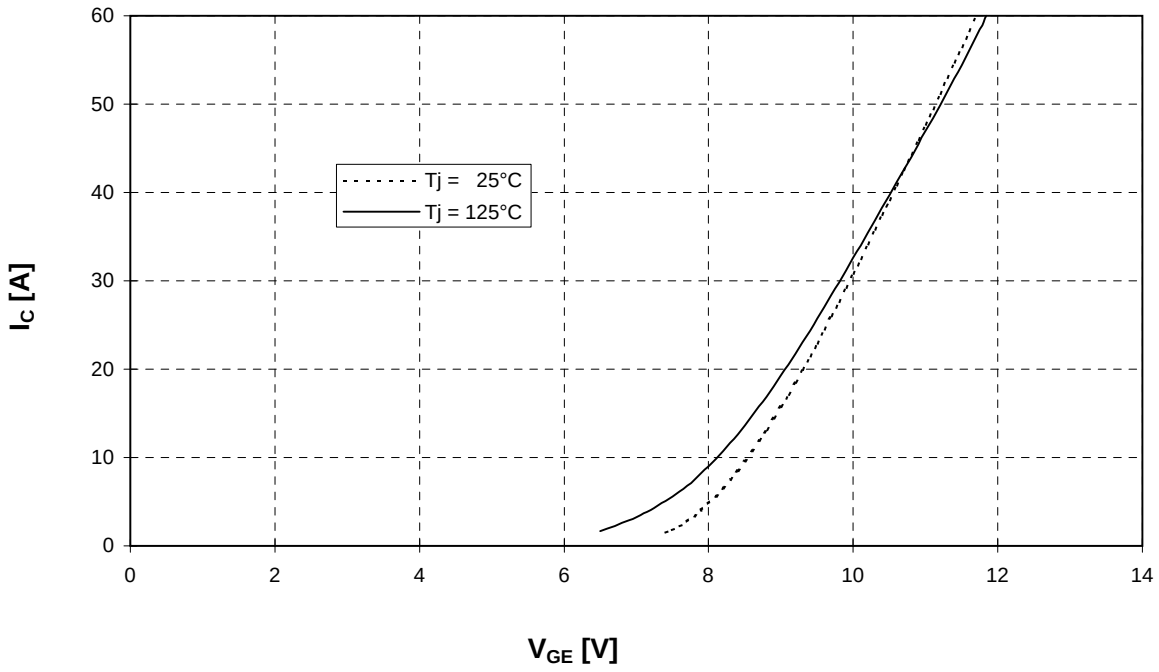
Ausgangskennlinienfeld Wechselr. (typisch) $I_C = f(V_{CE})$

Output characteristic Inverter (typical) $T_{vj} = 125°C$



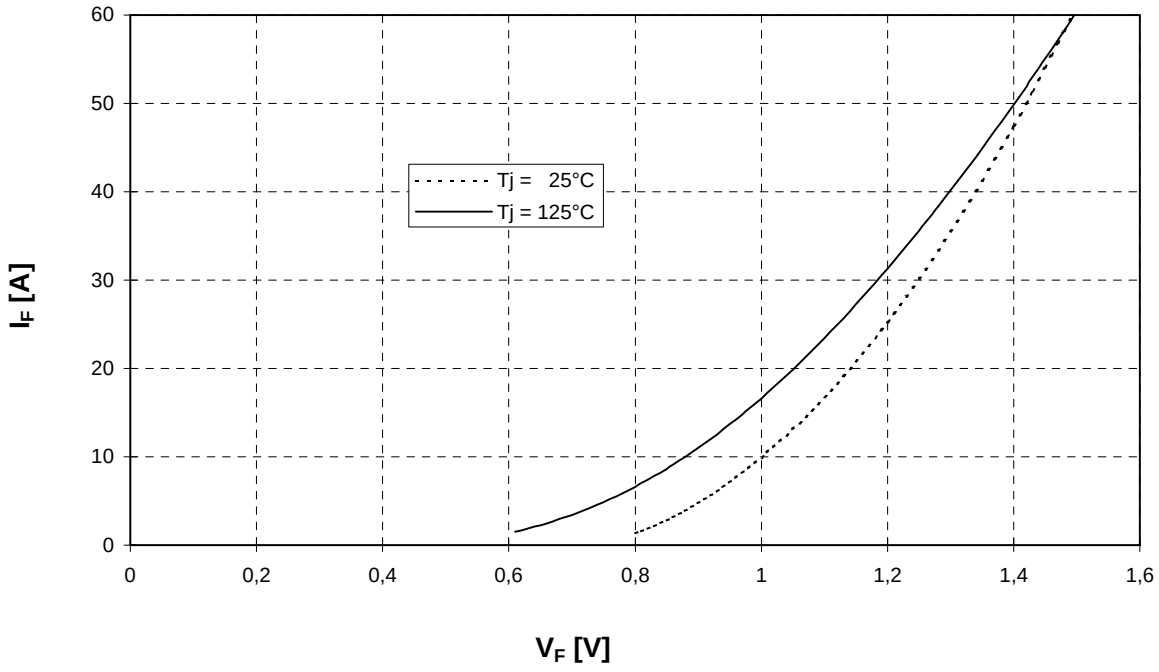
Übertragungscharakteristik Wechselr. (typisch) $I_C = f(V_{GE})$

Transfer characteristic Inverter (typical) $V_{CE} = 20\ V$



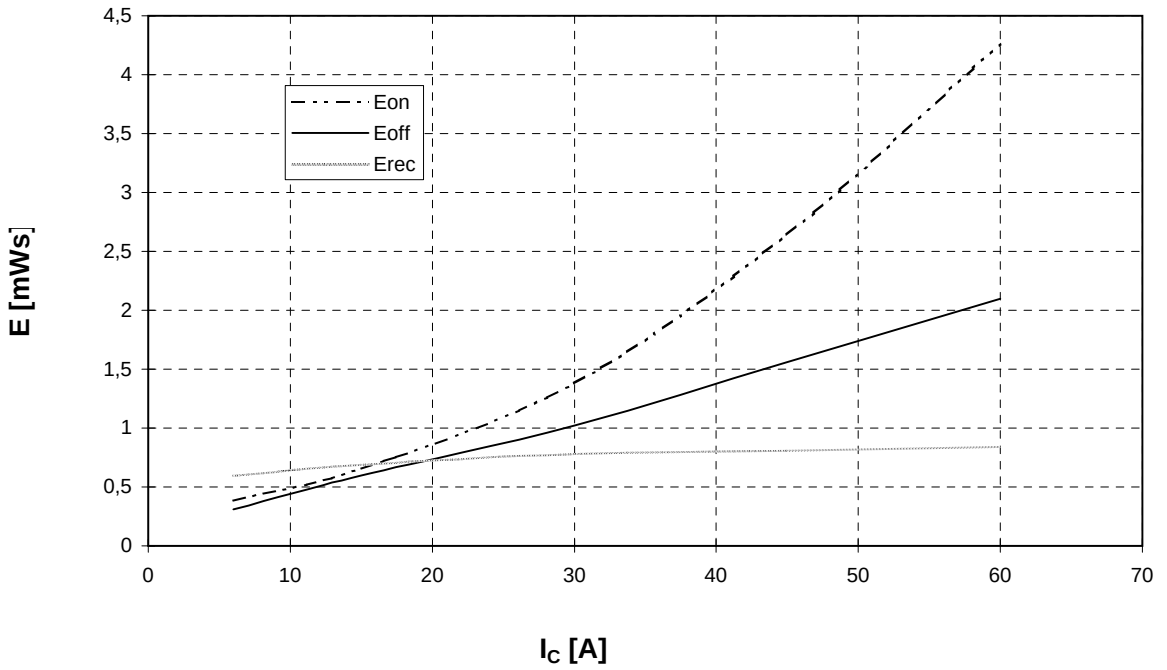
Durchlaßkennlinie der Freilaufdiode Wechselr. (typisch) $I_F = f(V_F)$

Forward characteristic of FWD Inverter (typical)



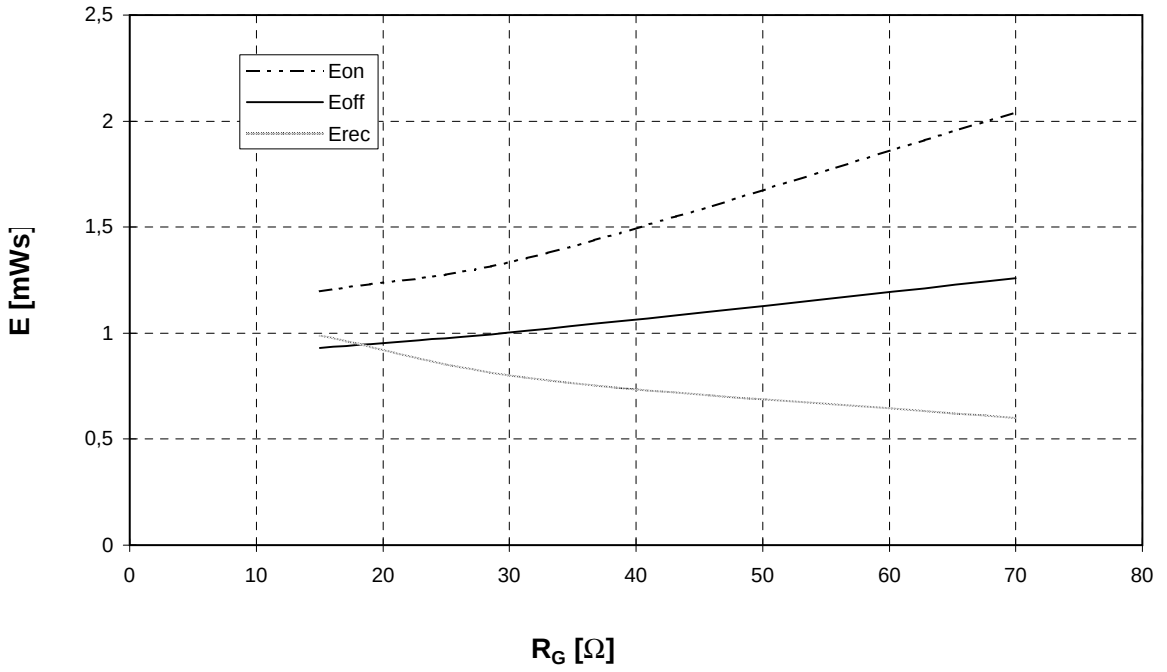
Schaltverluste Wechselr. (typisch) $E_{on} = f(I_C)$, $E_{off} = f(I_C)$, $E_{rec} = f(I_C)$ V_{CC} = **300 V**

Switching losses Inverter (typical) T_j = 125°C, V_{GE} = ±15 V, R_{Gon} = R_{Goff} = **33 Ohm**



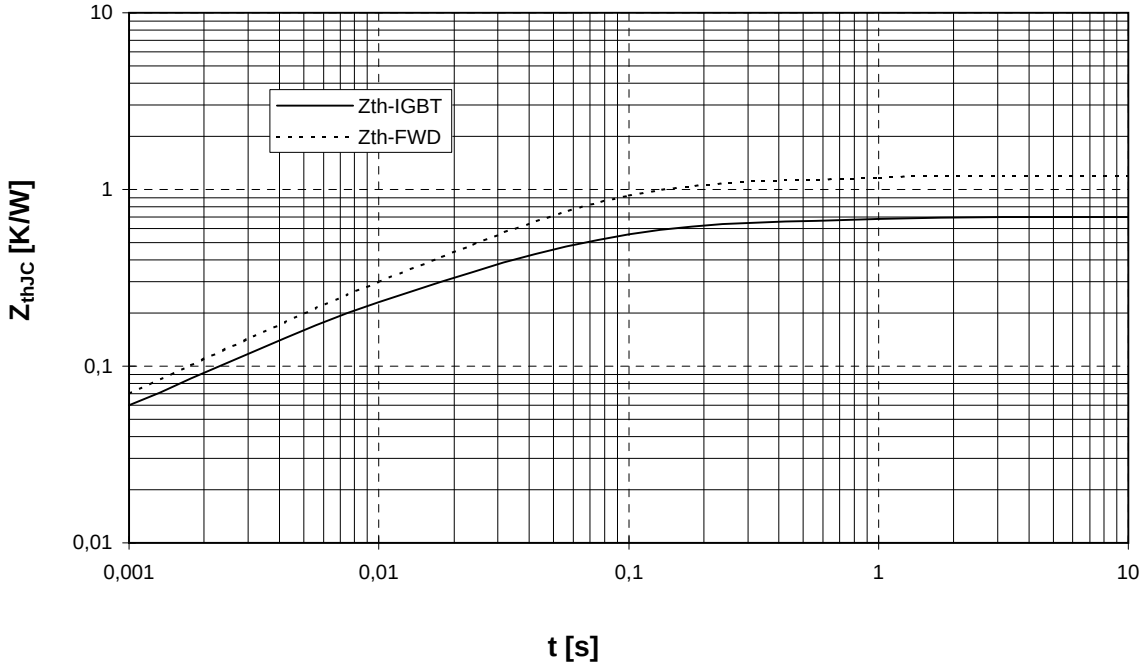
Schaltverluste Wechselr. (typisch) $E_{on} = f(R_G)$, $E_{off} = f(R_G)$, $E_{rec} = f(R_G)$

Switching losses Inverter (typical) T_j = 125°C, V_{GE} = +-15 V , $I_c = I_{nenn}$, V_{CC} = **300 V**



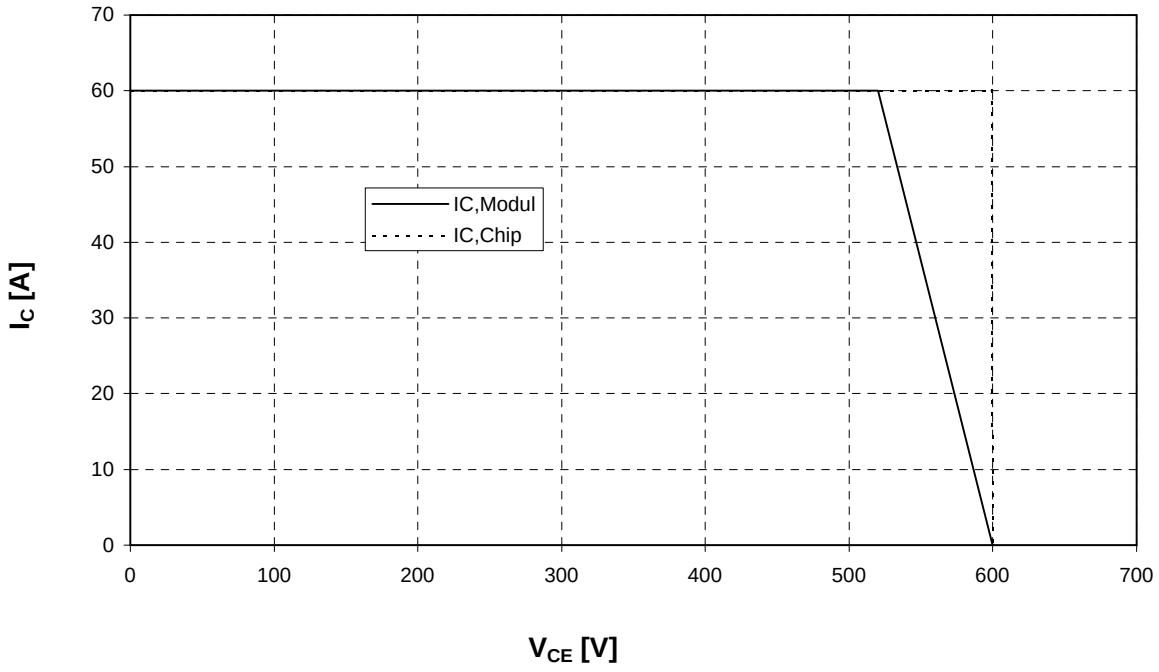
Transienter Wärmewiderstand Wechselr. $Z_{thJC} = f(t)$

Transient thermal impedance Inverter



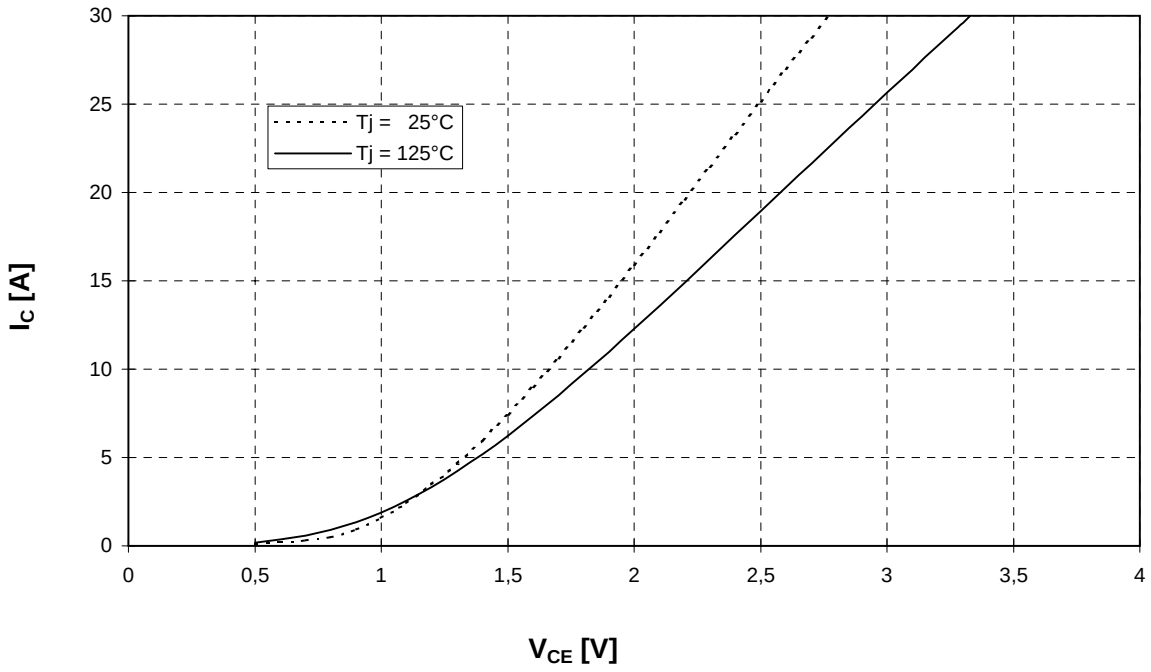
Sicherer Arbeitsbereich Wechselr. (RBSOA) $I_C = f(V_{CE})$

Reverse bias save operating area Inverter (RBSOA) $T_{vj} = 125°C$, $V_{GE} = \pm 15V$, $R_G =$ **33 Ohm**



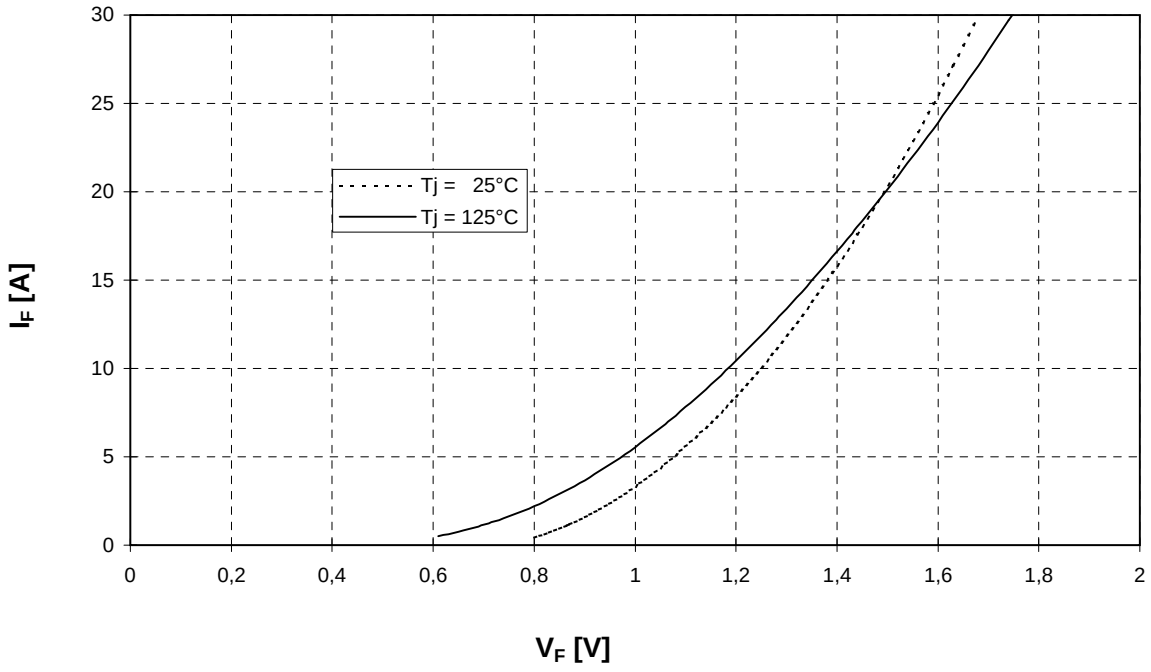
Ausgangskennlinienfeld Brems-Chopper-IGBT (typisch) $I_C = f(V_{CE})$

Output characteristic brake-chopper-IGBT (typical) $V_{GE} = 15\ V$

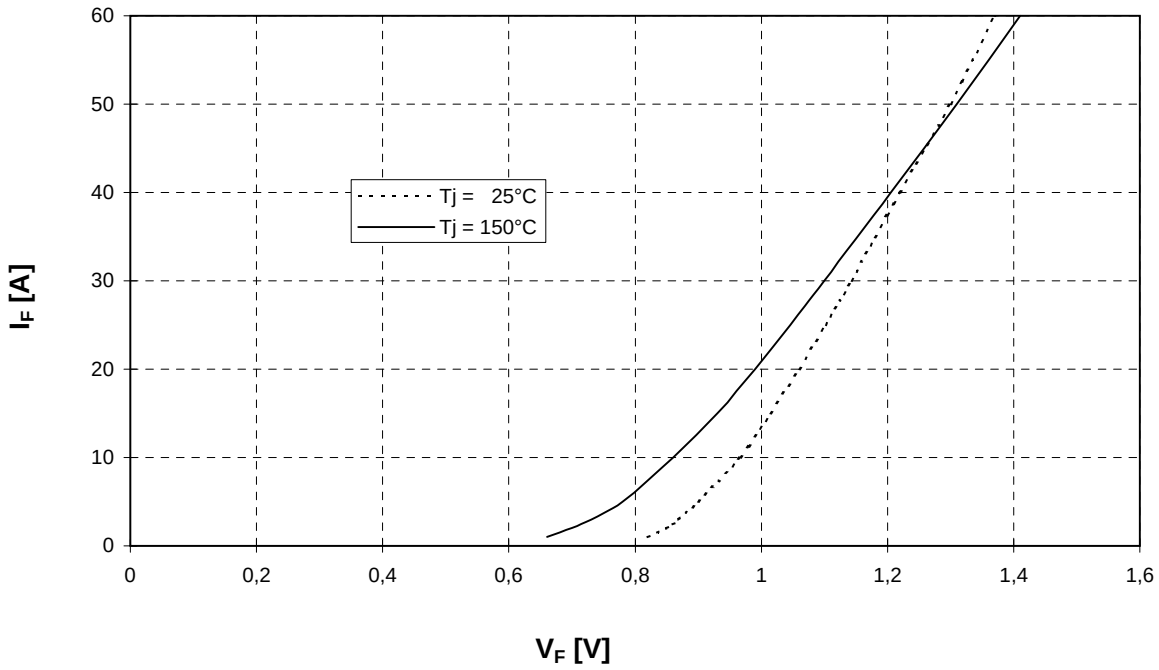


Durchlaßkennlinie der Brems-Chopper-Diode (typisch) $I_F = f(V_F)$

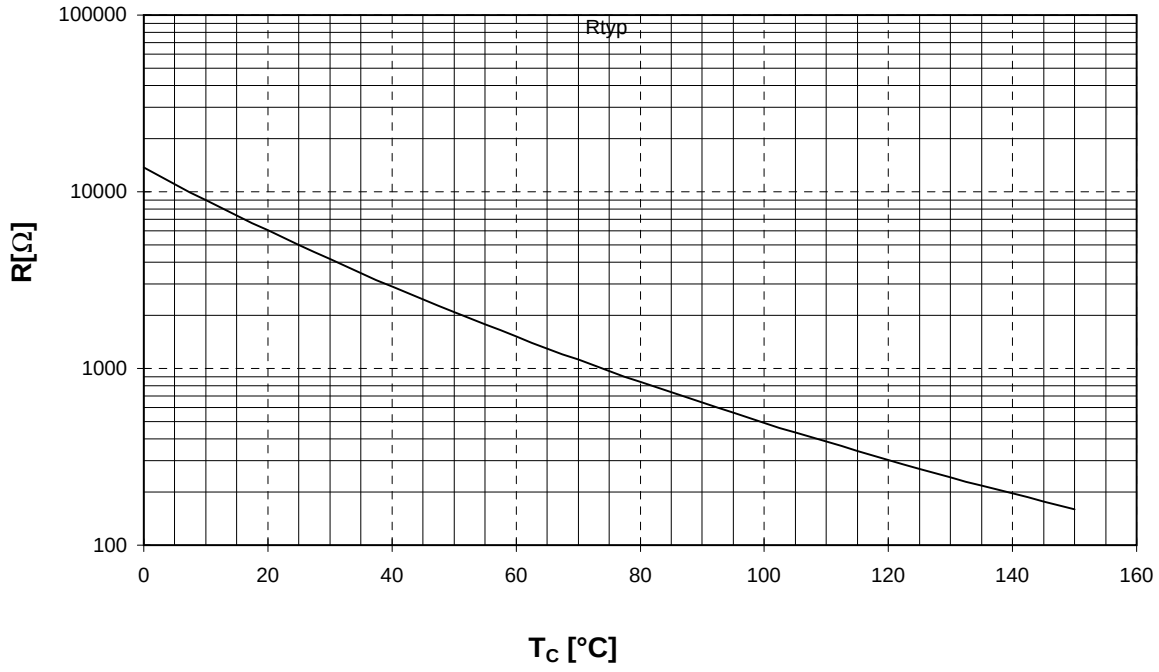
Forward characteristic of brake-chopper-FWD (typical)



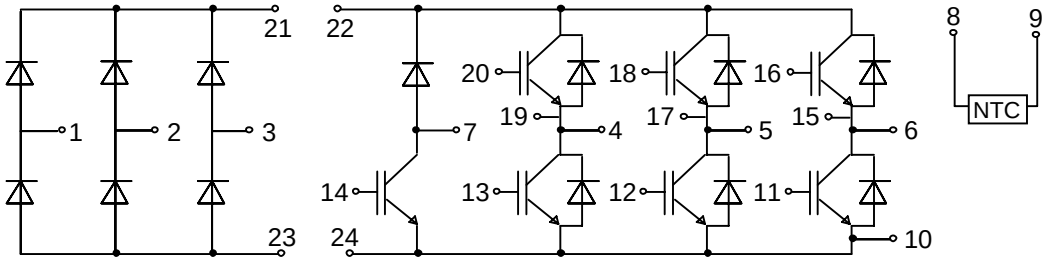
Durchlaßkennlinie der Gleichrichterdiode (typisch) $I_F = f(V_F)$
Forward characteristic of Rectifier Diode (typical)



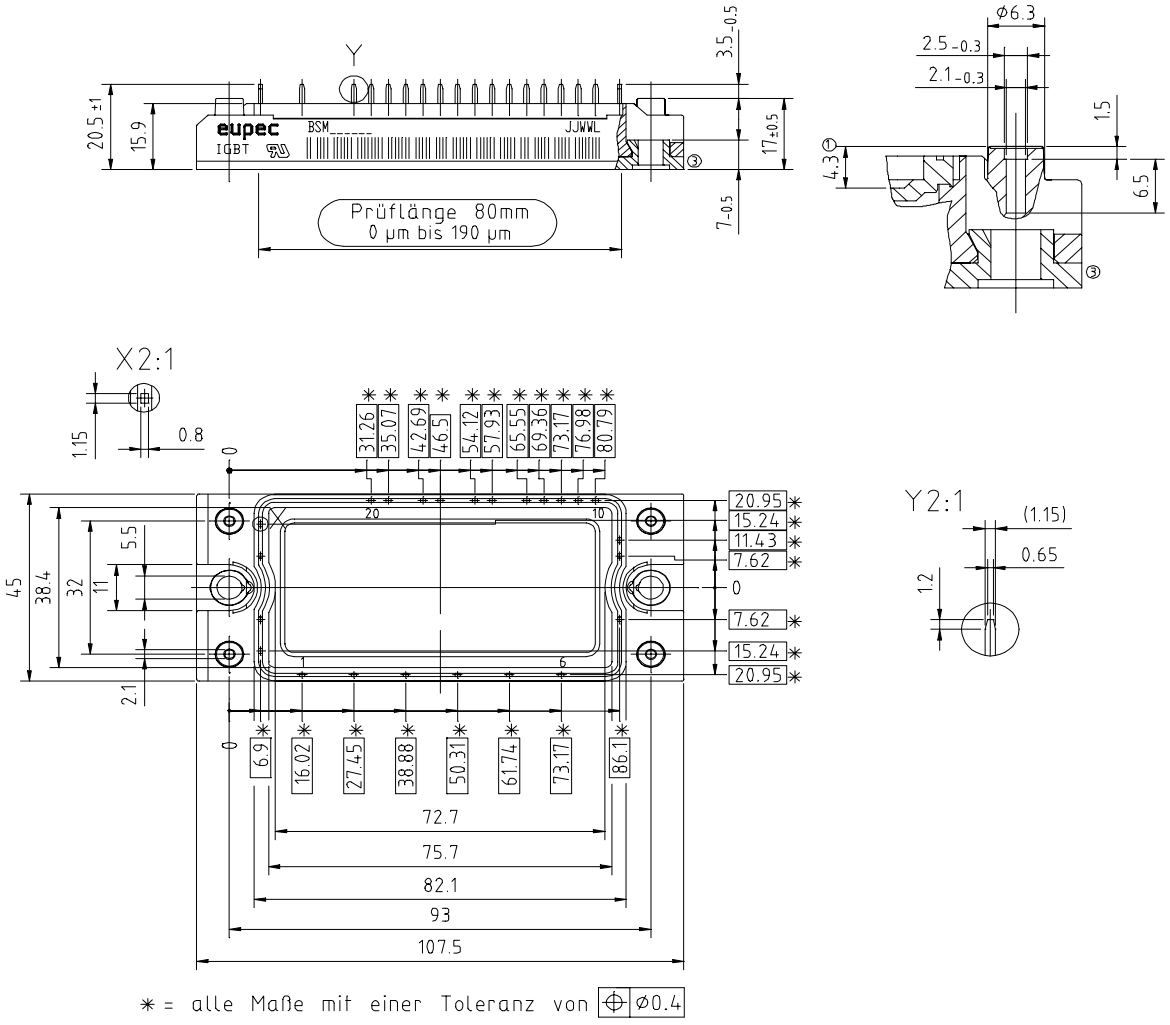
NTC- Temperaturkennlinie (typisch) **R = f (T)**
NTC- temperature characteristic (typical)



Schaltplan/ Circuit diagram



Gehäuseabmessungen/ Package outlines



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- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
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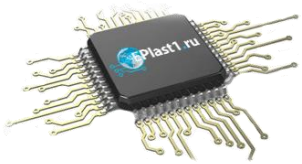
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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